Silicon Diffused Power Transistor BU508DW

GENERAL DESCRIPTION

High voltage, high-speed switching npn transistors in a plastic envelope with integrated efficiency diode, primarily for use in horizontal deflection circuits of colour television receivers.

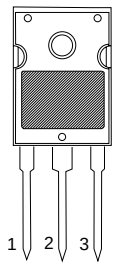
QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0 V	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	700	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	15	A
P_{tot}	Total power dissipation	$T_{mb} \leq 25$ ˚C	-	125	W
V_{CEsat}	Collector-emitter saturation voltage	I_C = 4.5 A; I_B = 1.6 A	-	1.0	V
I_{Csat}	Collector saturation current	f = 16kHz	4.5	-	A
V_F	Diode forward voltage	I_F = 4.5 A	1.6	2.0	V
t_f	Fall time	I_{Csat} = 4.5 A; f = 16kHz	0.7	-	µs

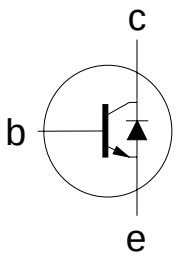
PINNING - SOT429

PIN	DESCRIPTION
1	base
2	collector
3	emitter
tab	collector

PIN CONFIGURATION



SYMBOL



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum Rating System (IEC 134)

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CESM}	Collector-emitter voltage peak value	V_{BE} = 0 V	-	1500	V
V_{CEO}	Collector-emitter voltage (open base)		-	700	V
I_C	Collector current (DC)		-	8	A
I_{CM}	Collector current peak value		-	15	A
I_B	Base current (DC)		-	4	A
I_{BM}	Base current peak value		-	6	A
P_{tot}	Total power dissipation	$T_{mb} \leq$ 25 ˚C	-	125	W
T_{stg}	Storage temperature		-65	150	˚C
T_j	Junction temperature		-	150	˚C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Junction to mounting base	-	-	1.0	K/W
$R_{th\ j\text{-}a}$	Junction to ambient	in free air	45	-	K/W

STATIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CES}	Collector cut-off current [1]	V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$	-	-	1.0	mA
I_{CES}		V_{BE} = 0 V; V_{CE} = $V_{CESMmax}$; T_j = 125 ˚C	-	-	2.0	mA
$V_{CEOsust}$	Collector-emitter sustaining voltage	I_B = 0 A; I_C = 100 mA; L = 25 mH	700	-	-	V
V_{CEsat}	Collector-emitter saturation voltages	I_C = 4.5 A; I_B = 1.6 A	-	-	1.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C = 4.5 A; I_B = 2 A	-	-	1.1	V
h_{FE}	DC current gain	I_C = 100 mA; V_{CE} = 5 V	6	13	30	
V_F	Diode forward voltage	I_F = 4.5 A	-	1.6	2.0	V

DYNAMIC CHARACTERISTICS

T_{mb} = 25 ˚C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
f_T	Transition frequency at f = 5 MHz	I_C = 0.1 A;V_{CE} = 5 V	7	-	MHz
C_C	Collector capacitance at f = 1MHz	V_{CB} = 10 V	125	-	pF
	Switching times (16 kHz line deflection circuit)	I_{Csat} = 4.5 A;L_c= 1 mH;C_{fb} = 4 nF $I_{B(end)}$ = 1.4 A; L_B = 6 µH; -V_{BB} = -4 V;			
t_s	Turn-off storage time		6.5	-	µs
t_f	Turn-off fall time		0.7	-	µs

1 Measured with half sine-wave voltage (curve tracer).

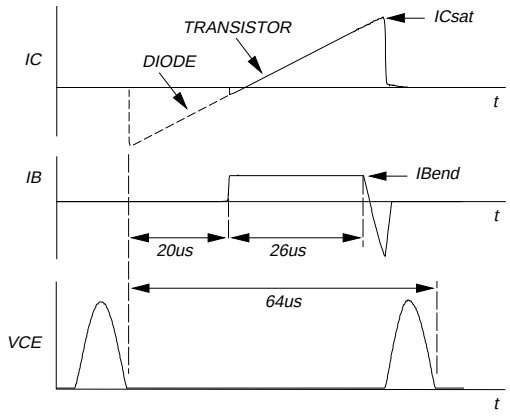


Fig.1. Switching times waveforms.

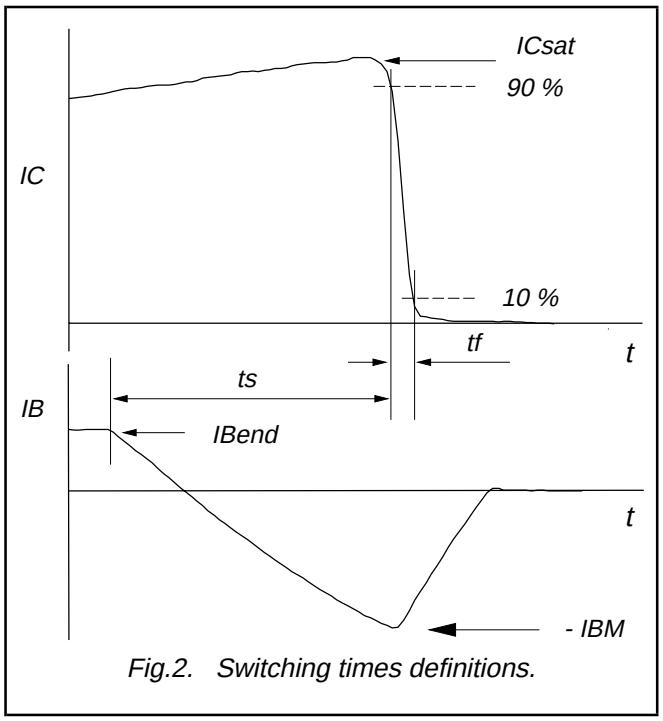


Fig.2. Switching times definitions.

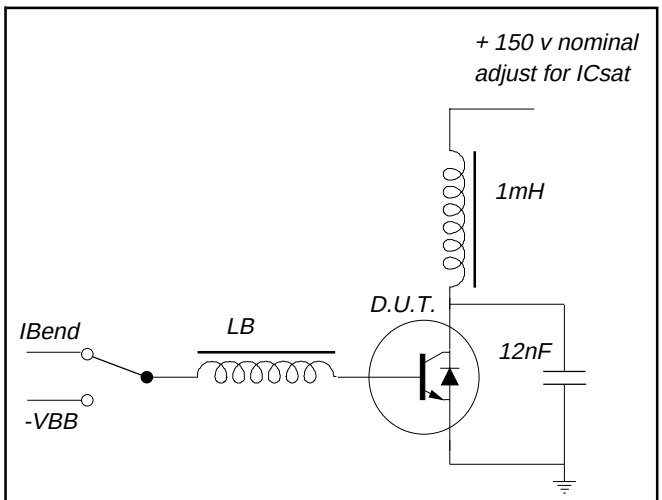


Fig.3. Switching times test circuit

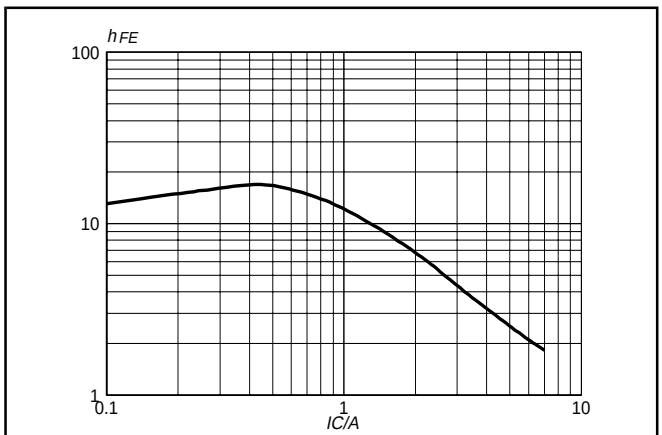


Fig.4. Typical DC current gain. $h_{FE} = f(I_C)$ parameter V_{CE}

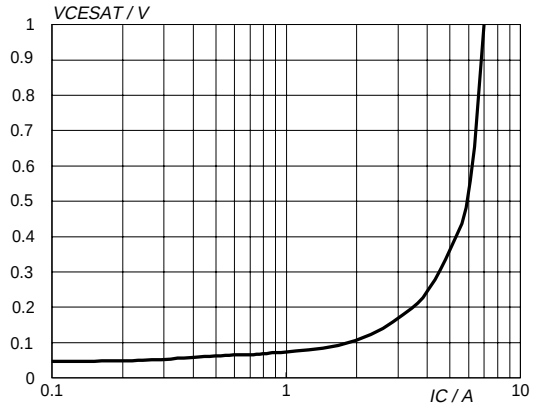


Fig.5. Typical collector-emitter saturation voltage. $V_{CE}sat = f(I_C)$; parameter I_C/I_B

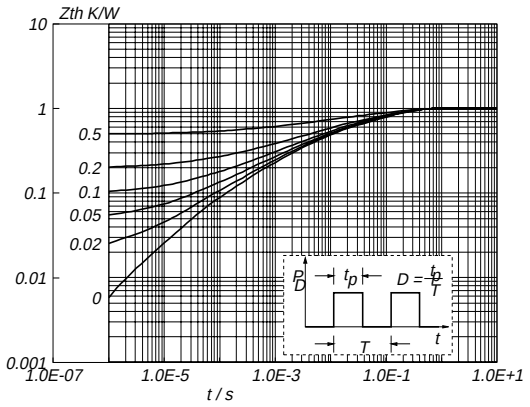


Fig.8. Transient thermal impedance. $Z_{th\ j\text{-}hs} = f(t)$; parameter $D = t_p/T$

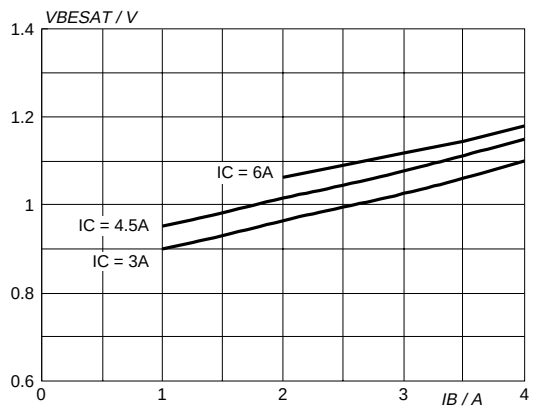


Fig.6. Typical base-emitter saturation voltage. $V_{BE}sat = f(I_B)$; parameter I_C

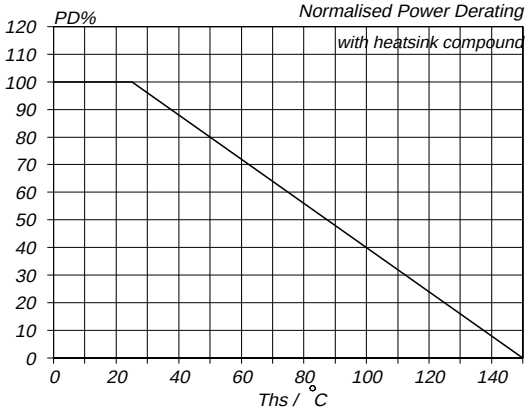


Fig.9. Normalised power dissipation. $PD\% = 100 \cdot P_D/P_{D\ 25^\circ C} = f(T_{hs})$

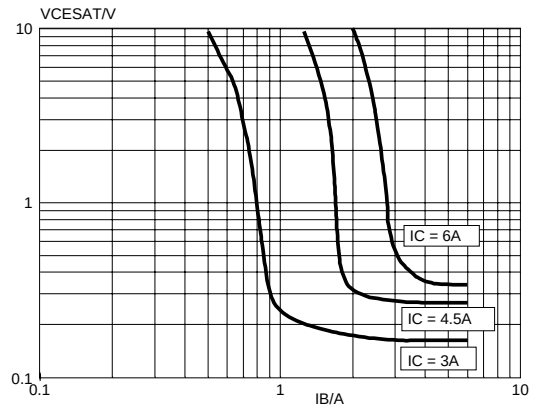


Fig.7. Typical collector-emitter saturation voltage. $V_{CE}sat = f(I_B)$; parameter I_C

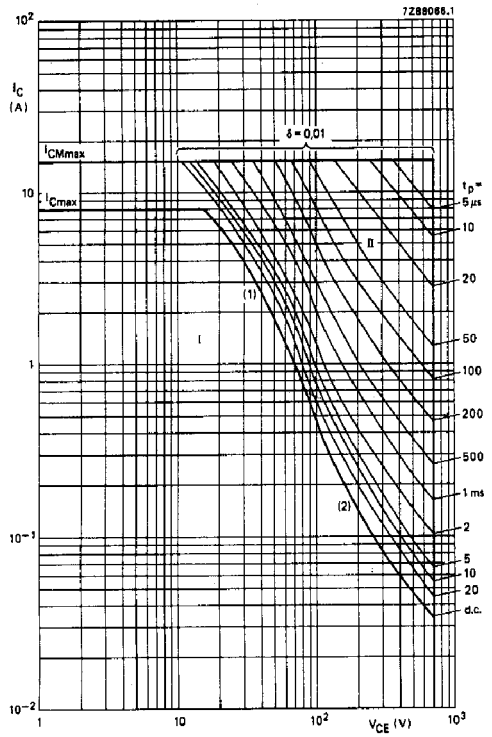


Fig.10. Forward bias safe operating area. T_{hs} < 25˚C
(1) *$P_{tot\ max}$ line.*
(2) *Second-breakdown limits (independent of temperature).*
I *Region of permissible DC operation.*
II *Permissible extension for repetitive pulse operation.*

MECHANICAL DATA

Dimensions in mm

Net Mass: 5 g

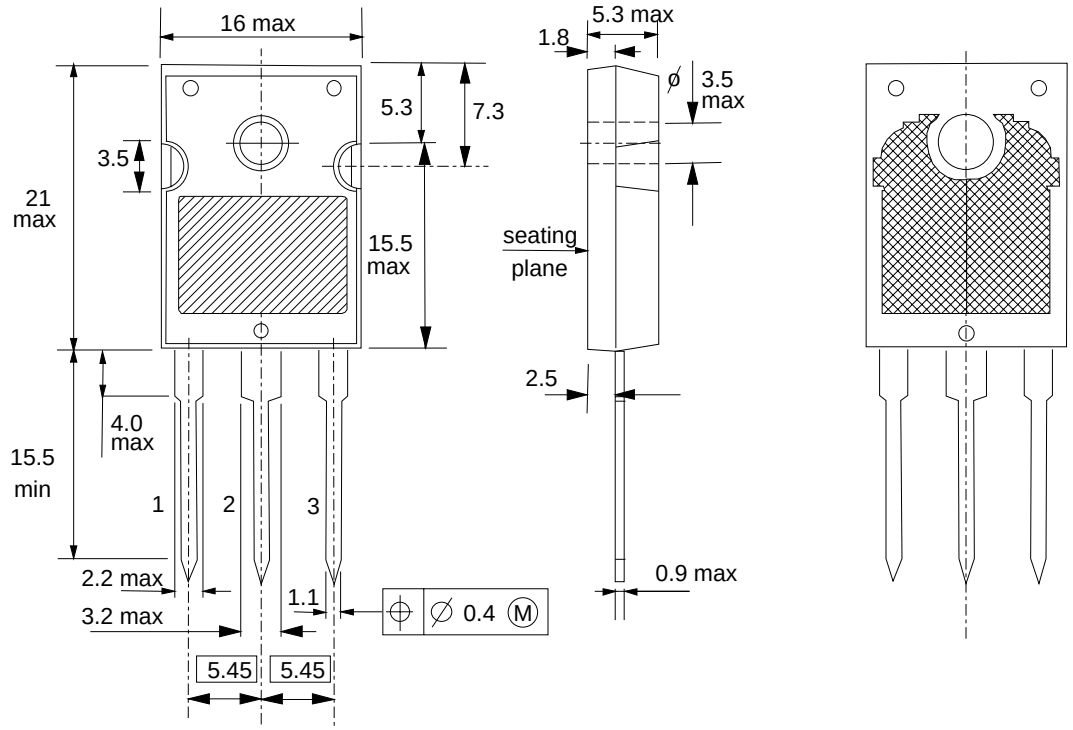


Fig.11. SOT429; pin 2 connected to mounting base.

Notes
1. Refer to mounting instructions for SOT429 envelope.
2. Epoxy meets UL94 V0 at 1/8".

DEFINITIONS

Data sheet status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values are given in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of this specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

LIFE SUPPORT APPLICATIONS

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